

# STV9379FA

# **VERTICAL DEFLECTION BOOSTER**

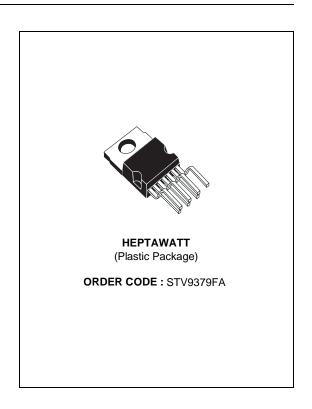
- POWER AMPLIFIER
- THERMAL PROTECTION
- OUTPUT CURRENT UP TO 2.6APP
- FLYBACK VOLTAGE UP TO 90V (on Pin 5)
- SUITABLE FOR DC COUPLING APPLICATION
- EXTERNAL FLYBACK SUPPLY



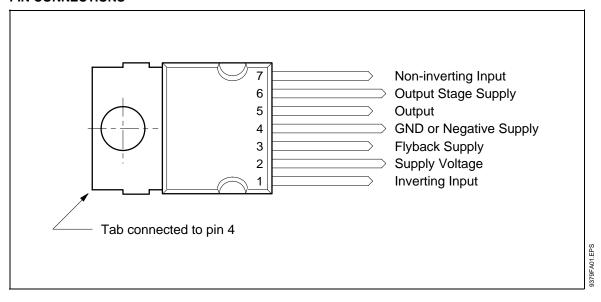
Designed for monitors and high performance TVs, the STV9379FA vertical deflection booster can handle flyback voltage up to 90V. Further to this, it is possible to have a flyback voltage which is more than the double of the supply (Pin 2). This allows to decrease the power consumption, or to decrease the flyback time for a given supply voltage.

The STV9379FA operates with supplies up to 42V and provides up to 2.6A<sub>PP</sub> output current to drive the yoke.

The STV9379FA is offered in HEPTAWATT package.

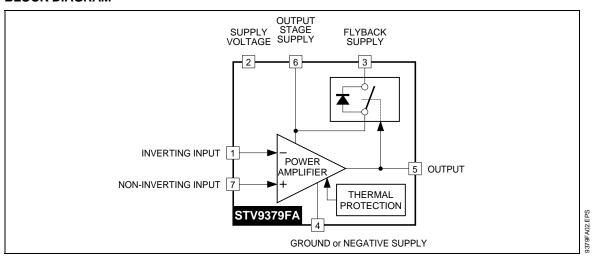


#### **PIN CONNECTIONS**



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#### **BLOCK DIAGRAM**



### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vs	Supply Voltage (Pin 2) (see note 1)	50	V
V <sub>6</sub>	Flyback Peak Voltage (Pin 6) (see note 1)	100	V
$V_1$ , $V_7$	Amplifier Input Voltage (Pins 1-7) (see note 1)	- 0.3, + V <sub>S</sub>	V
Ιο	Maximum Output Peak Current (see notes 2 and 3)	1.8	Α
l <sub>3</sub>	Maximum Sink Current (t < 1ms)	1.8	Α
l <sub>3</sub>	Maximum Source Current (t < 1ms) (in the diode, see Block Diagram) (see note 2)	1.8	А
V <sub>ESD</sub>	ESD susceptibility : EIAJ Norm (200pF discharged through $0\Omega$ )	300	V
V <sub>3</sub> - V <sub>2</sub>	Voltage Difference between Flyback Supply and Supply Voltage	50	V
T <sub>oper</sub>	Operating Ambient Temperature	- 20, + 75	°C
T <sub>stg</sub>	Storage Temperature	- 40, + 150	°C
Tj	Junction Temperature	+150	°C

Notes:

- Versus Pin 4. 1.
- The output current can reach 5A peak for t  $\leq$  10 $\mu$ s (up to 120Hz). Provided SOAR is respected (see Figures 1 and 2).

### THERMAL DATA

Symbol	Parameter	Value	Unit
R <sub>th (j-c)</sub>	Junction-case Thermal Resistance Max.	3	°C/W
Tt	Temperature for Thermal Shutdown	150	°C
$\Delta T_t$	Hysteresis on T <sub>t</sub>	10	°C
T <sub>jr</sub>	Recommended Max. Junction Temperature	120	°C

*5*7

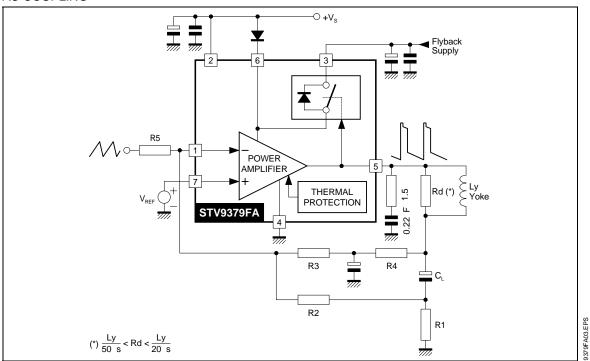
# **ELECTRICAL CHARACTERISTICS**

 $(V_S = 42V, T_A = 25^{\circ}C, unless otherwise specified)$ 

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Operating Supply Voltage Range	Versus Pin 4	10		42	V
V <sub>3M</sub>	Operating Flyback Supply Voltage (V <sub>3M</sub> ≤ V <sub>S</sub> + 50V)	Versus Pin 4	Vs		90	V
l <sub>2</sub>	Pin 2 Quiescent Current	$I_3 = 0, I_5 = 0$		13	20	mA
I <sub>6</sub>	Pin 6 Quiescent Current	$I_3 = 0, I_5 = 0$	5	10	30	mA
Ιο	Max. Operating Peak Output Current				1.3	Α
I <sub>1</sub>	Amplifier Bias Current	$V_1 = 22V, V_7 = 23V$		- 0.15	- 1	μΑ
l <sub>7</sub>	Amplifier Bias Current	$V_1 = 23V, V_7 = 22V$		- 0.15	- 1	μΑ
V <sub>IO</sub>	Offset Voltage				7	mV
$\Delta V_{IO}/dt$	Offset Drift versus Temperature			- 10		μV/°C
GV	Voltage Gain		80			dB
$V_{5L}$	Output Saturation Voltage to GND (Pin 4)	I <sub>5</sub> = 1.3A		1	1.6	V
$V_{5H}$	Output Saturation Voltage to Supply (Pin 6)	I <sub>5</sub> = - 1.3A		1.6	2.2	V
V <sub>D5 - 6</sub>	Diode Forward Voltage between Pins 5-6	I <sub>5</sub> = 1.3A		1.4	2.1	V
V <sub>D3 - 6</sub>	Diode Forward Voltage between Pins 3-6	I <sub>3</sub> = 1.3A		1.7	2.5	V
V <sub>3-6</sub>	Voltage Drop between Pins 3-6 (2nd part of flyback)	I <sub>3</sub> = - 1.3A		2.9	3.6	V

### **APPLICATION CIRCUITS**

# AC COUPLING



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### **APPLICATION CIRCUITS (continued)**

DC COUPLING

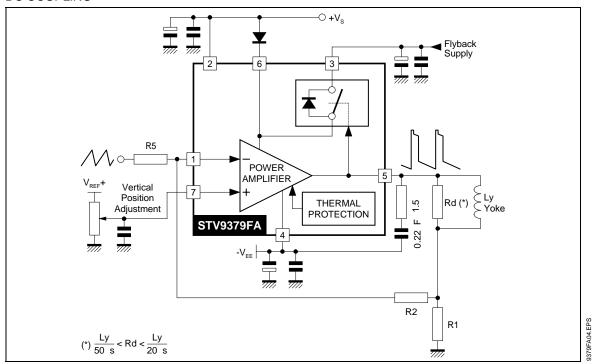


Figure 1: Output Transistors SOA (for secondary breakdown)

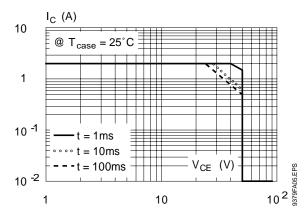
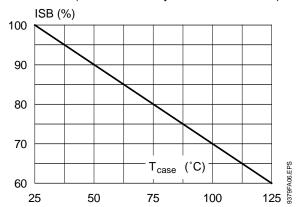
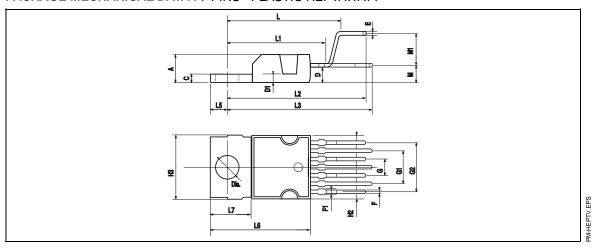


Figure 2: Secondary Breakdown Temperature
Derating Curve
(ISB = secondary breakdown current)



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# PACKAGE MECHANICAL DATA: 7 PINS - PLASTIC HEPTAWATT



Dimensions		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α			4.8			0.189
С			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		08	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		16.97			0.668	
L1		14.92			0.587	
L2		21.54			0.848	
L3		22.62			0.891	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
М		2.8			0.110	
M1		5.08			0.200	
Dia.	3.65		3.85	0.144		0.152

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